

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re the Application of: **Tsuguo FUKUDA et al.**

Application Number: **Not yet assigned**  
**(§371 of international application No. PCT/JP2005/000696)**

Filed: **July 19, 2006**

For: **PROCESS FOR PRODUCING SINGLE CRYSTAL OF GALLIUM-  
CONTAINING NITRIDE**

Attorney Docket Number: **062697**  
Customer Number: **38834**

**INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

July 19, 2006

Sir:

In compliance with 37 C.F.R. §1.56, Applicants direct the attention of the Patent and Trademark Office to the documents listed on the attached PTO/SB/08. A copy of each non- U.S. document is enclosed herewith as well as an International Search Report mailed April 5, 2005.

If there are any fees due in connection with the filing of this paper, please charge Deposit Account No. 50-2866.

Respectfully submitted,

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Enclosure: PTO/SB/08, Documents (8) & Int'l Search Report

10/586581

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<b>Combined Form PTO/SB/08A&amp;B</b>  <b><u>INFORMATION DISCLOSURE</u></b> <b><u>STATEMENT BY APPLICANT</u></b>  <i>(use as many sheets as necessary)</i>			<i>Complete if Known</i>		
			Application Number	Not yet assigned	
			Confirmation Number		
			Filing Date	July 19, 2006	
			First Named Inventor	Tsuguo FUKUDA et al.	
			Art Unit		
Examiner Name					
Sheet	1	of	1	Attorney Docket Number	062697

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code <sup>2</sup> (if known)		
	1	US 6,273,948	B1	8/14/2001	Porowski et al.
	2	US 6,270,569	B1	8/7/2001	Shibata et al.
	3	US 6,592,663	B1	7/15/2003	Sarayama et al.
	4	US 5,363,799		11/15/1994	Yonehara et al.
	5	US 2004/0144300	A1	7/29/2004	Kitaoka et al.

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation <sup>6</sup>
		Country Code <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)			
	6	JP	56-160400	A	12/10/1981	Matsushita Electrical Industrial Co., Ltd.	Abstract; Cited in ISR
	7	JP	1-132117	A	5/24/1989	Canon Inc.	Abstract; Cited in ISR; Corresponds to #4
	8	JP	2004-244307	A	9/2/2004	Matsushita Electric Industrial Co., Ltd.	Abstract; Cited in ISR; Corresponds to #5
	9	JP	2001-131741	A	5/15/2001	Sony Corp	Abstract; Cited in ISR

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation <sup>6</sup>
	10	M.K. KELLY et al., "Optical patterning of GaN films", Appl. Phys. Lett. 69 (12), 16 September 1996	
	11	W.S. WONG et al., "Fabrication of thin-film InGaN light-emitting diode membranes by laser lift-off", Applied Physics Letters, Volume 75, Number 10, 6 September 1999	
	12	TAKAYUKI INOUE et al., "Growth of Bulk GaN Single Crystals by the Pressure-Controlled...", Central R&D Laboratory, Japan Energy Corporation, Faculty of Engineering, Yamaguchi University, May 15, 2000	
	13	S. POROWSKI et al., "Thermodynamical properties of III-V nitrides and crystal growth of...", Journal of Crystal Growth 178 (1997) 174-188	
	14	International Search Report mailed April 5, 2005 of International Application PCT/JP2005/000696	

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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